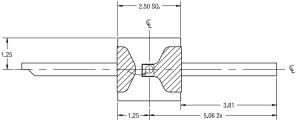
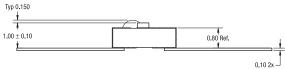
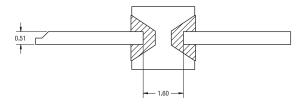
■FCI-InGaAs-XXX-LCER

High Speed InGaAs Photodiodes Mounted on Ceramic Packages w/Leads

FCI-InGaAs-XXX-LCER with active area sizes of 70µm, 120µm, 300µm, 400μm and 500μm are part of OSI Optoelectronics's high speed IR sensitive photodiodes mounted on gull wing ceramic substrates. The chips can be epoxy/eutectic mounted onto the ceramic substrate.

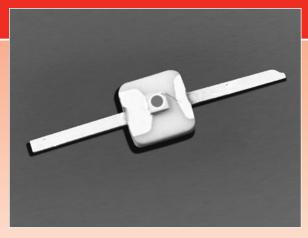






Notes:

- · All units in millimeters.
- All devices are mounted with low out gassing conductive epoxy with tolerance of ±25µm. Eutectic mounting is also available upon request.



APPLICATIONS

- High Speed Optical Communications
- Gigabit Ethernet/Fibre Channel
- SONET / SDH, ATM
- Diode Laser Monitoring
- Instrumentation

FEATURES

- Low Noise
- High Responsivity
- High Speed
- Spectral Range 900nm to 1700nm

Absolute Maximum Ratings											
PARAMETERS	SYMBOL	MIN	MAX	UNITS							
Storage Temperature	T _{stg}	-40	+85	°C							
Operating Temperature	T _{op}	0	+70	°C							
Soldering Temperature	T _{sld}		+260	°C							

Electro-Op	Electro-Optical Characteristics T _A =23°													23°C				
PARAMETERS	SYMBOL	CONDITIONS	FCI-InGaAs-70LCER		FCI-InGaAs-120LCER		FCI-InGaAs-300LCER		FCI-InGaAs-400LCER			FCI-InGaAs-500LCER			UNITS			
			MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	ONTIS
Active Area Diameter	AA_{ϕ}			70			120			300			400			500		μm
Responsivity	R _λ	λ=1310nm	0.80	0.90		0.80	0.90		0.80	0.90		0.80	0.90		0.80	0.90		A/W
		λ=1550nm	0.90	0.95		0.90	0.95		0.90	0.95		0.90	0.95		0.90	0.95		
Capacitance	C _j	V _R = 5.0V		0.65			1.0			10.0			14.0			20.0		pF
Dark Current	I _d	V _R = 5.0V		0.03	2		0.05	2		0.30	5		0.40	5		0.50	20	nA
Rise Time/ Fall Time	t _r /t _f	$V_R = 5.0V,$ $R_L = 50\Omega$ 10% to 90%			0.20			0.30			1.5			3.0			10.0	ns
Max. Revervse Voltage					20			20			15			15			15	V
Max. Reverse Current					1			2			2			2			2	mA
Max. Forward Current					5			5			8			8			8	mA
NEP				3.44E- 15			4.50E- 15			6.28E- 15			7.69E- 15			8.42E- 15		W/√Hz